TOSHIBA VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

1 S V 2 1 4

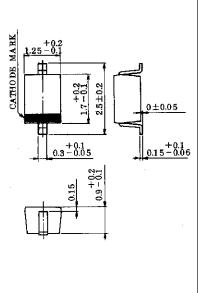
TV TUNING.

Unit in mm

- High Capacitance Ratio: C2V/C25V=6.5 (Typ.)
- Low Series Resistance : $r_S = 0.4\Omega$ (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for Small Size Tuner.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	$v_{ m R}$	30	V
Peak Reverse Voltage	v_{RM}	$(R_L = 10 \mathrm{k}\Omega)$	v
Junction Temperature	$T_{ m j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C



JEDEC	_	
EIAJ	_	
TOSHIBA	1-1E1A	

Weight: 0.004g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	$V_{\mathbf{R}}$	$I_R = 1 \mu A$	30	_	_	V
Reverse Current	$I_{ m R}$	$V_R=28V$	_		10	nА
Capacitance	C2V	$V_R=2V$, $f=1MHz$	14.16	_	16.25	рF
Capacitance	C25V	V_R =25V, f=1MHz	2.11		2.43	рF
Capacitance Ratio	C2V / C25V		5.90	6.50	7.15	_
Series Resistance	\mathbf{r}_{S}	V_R =5V, f=470MHz	_	0.4	0.55	Ω

Note 1: Units are compounded in one package and are matched to 2.5%.

$$\frac{\text{C(Max.)} - \text{C(Min.)}}{\text{C(Min.)}} \leq 0.025$$

$$(\text{V}_R = 2 \sim 25\text{V})$$

Marking

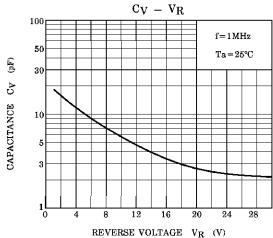


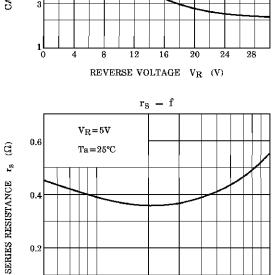
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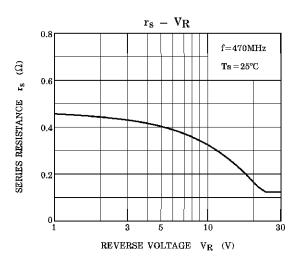
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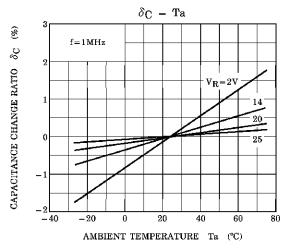




FREQUENCY f (MHz)

1000





NOTE:
$$\delta_{C} = \frac{C (Ta) - C (25)}{C (25)} \times 100$$